Features

- Advanced Trench Process Technology
- Low Threshold Voltage
- Fast Switching Speed
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel MOSFET

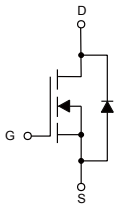
Maximum Ratings

- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Thermal Resistance: 357°C/W Junction to Ambient(2)

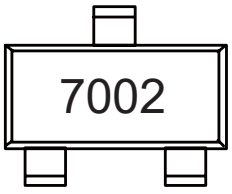
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous	TA=25°C @ Steady State	I_D	0.34	A
	TA=100°C @ Steady State		0.2	
Pulsed Drain Current		I_{DM}	1.5	A
Power Dissipation		P_D	0.35	W

Note: 1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

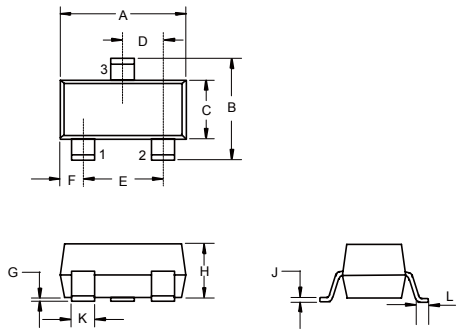
Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN

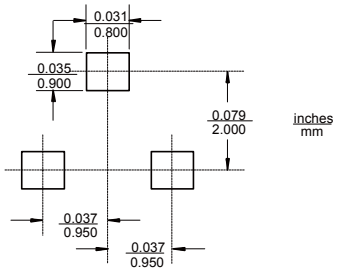


SOT-23



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=10μA	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.0		2.5	V
Gate-Body Leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±20V			±10	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =60V, V_{GS} =0V			80	nA
		V_{DS} =60V, V_{GS} =0V,T_J=125 °C			1.0	μA
On-State Drain Current	$I_{D(on)}$	V_{DS} =7.5V, V_{GS} =10V	500	2700		mA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=500mA		1.2	5	Ω
		V_{GS}=5V, I_D=50mA		1.7	7.5	
Drain-Source On-Voltage	$V_{DS(on)}$	V_{GS}=10V, I_D=500mA			3.75	V
		V_{GS}=5V, I_D=50mA			1.5	
Forward Transconductance	g_{fs}	V_{DS} =10V, I_D =200mA	80			ms
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=115mA			1.5	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				115	mA
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V, f=1MHz			50	pF
Output Capacitance	C_{oss}				25	
Reverse Transfer Capacitance	C_{rss}				5	
Turn-On Time	$t_{d(on)}$	V_{DD}=30V,V_{GEN}=10V,R_L=150Ω, I_D=200mA,R_{GEN}=25Ω		3.3	20	ns
Turn-Off Time	$t_{d(off)}$			9.6	20	

Curve Characteristics

Fig. 1 - Output Characteristics

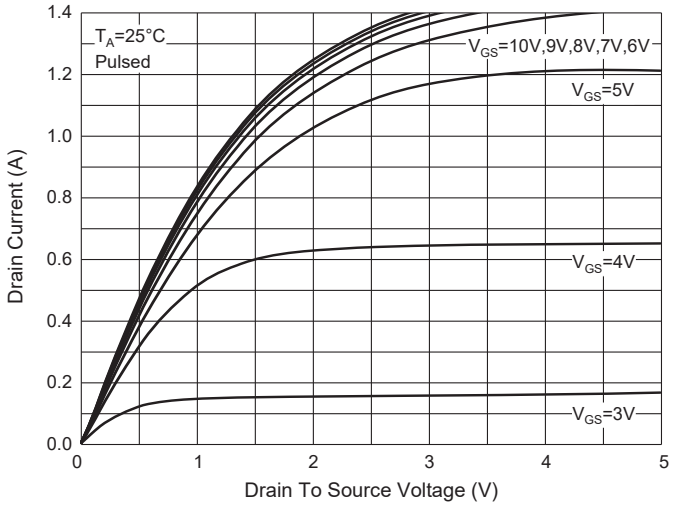


Fig. 2 - Transfer Characteristics

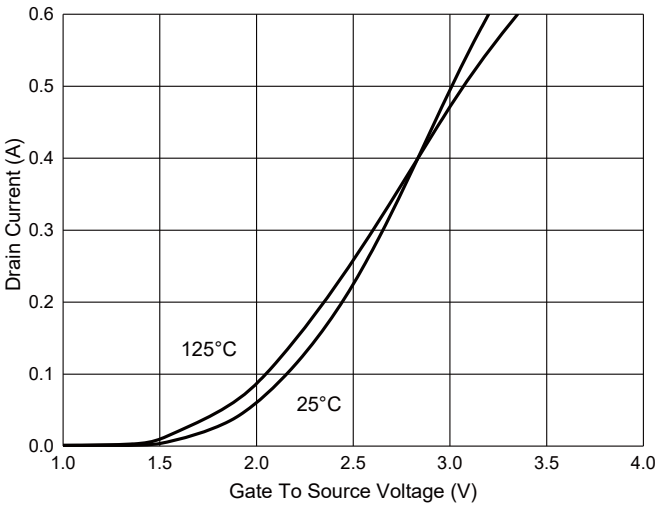


Fig. 3 - $R_{DS(ON)}$—I_D

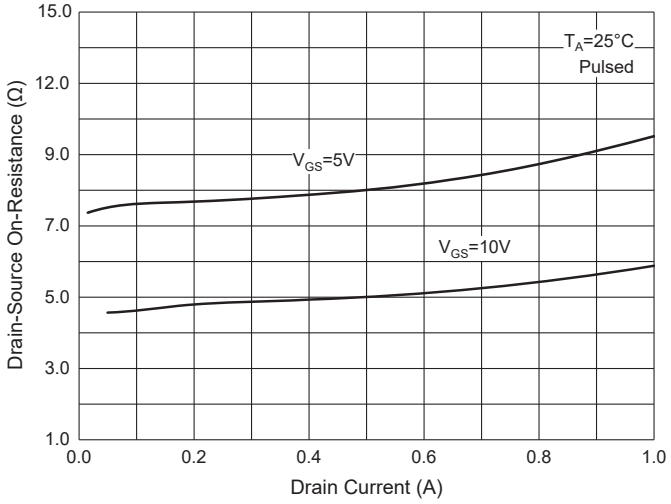


Fig. 3 - $R_{DS(ON)}$—V_{GS}

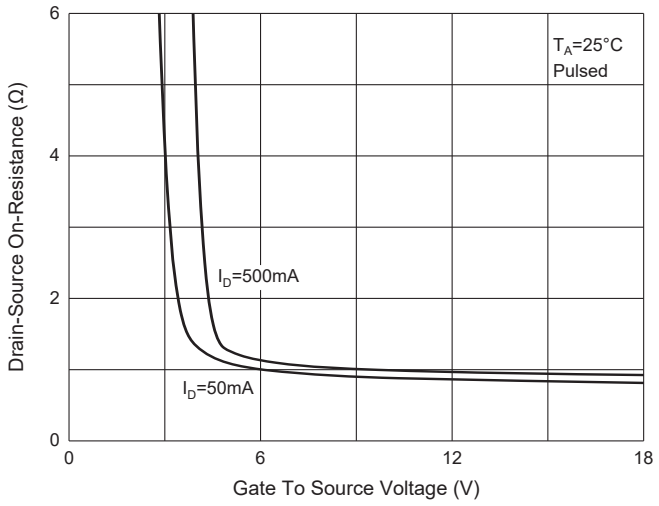
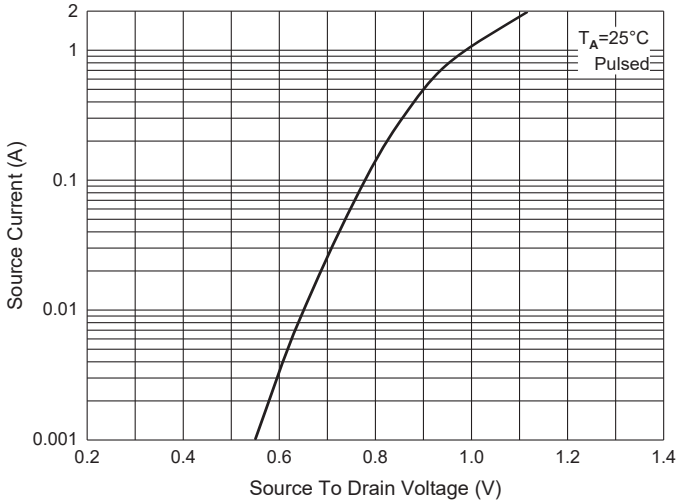


Fig. 5 - I_S—V_{SD}



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel